

### SOT-363 Plastic-Encapsulate Transistors

TRANSISTOR (NPN+NPN)

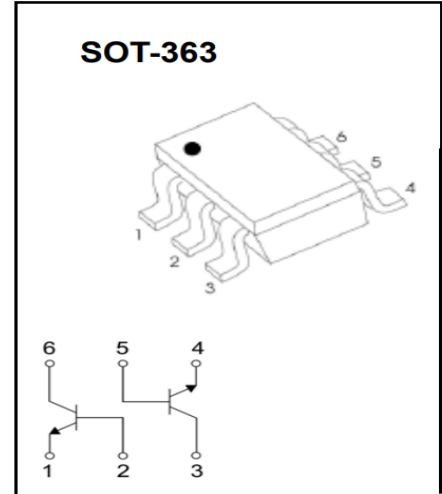
#### FEATURES

- High current.
- Low  $V_{CE(sat)}$ .  $V_{CE(sat)} \leq 250\text{mV}$  at  $I_C = 200\text{mA} / I_B = 10\text{mA}$

MARKING: BX

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector- Base Voltage	15	V
$V_{CEO}$	Collector-Emitter Voltage	12	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	0.5	A
$P_C$	Collector Power Dissipation	0.15	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	15			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	12			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=15\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=2\text{V}, I_C=10\text{mA}$	270		680	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200\text{mA}, I_B=10\text{mA}$			0.25	V
Transition frequency	$f_T$	$V_{CE}=2\text{V}, I_C=10\text{mA}, f=100\text{MHz}$		320		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		7.5		pF



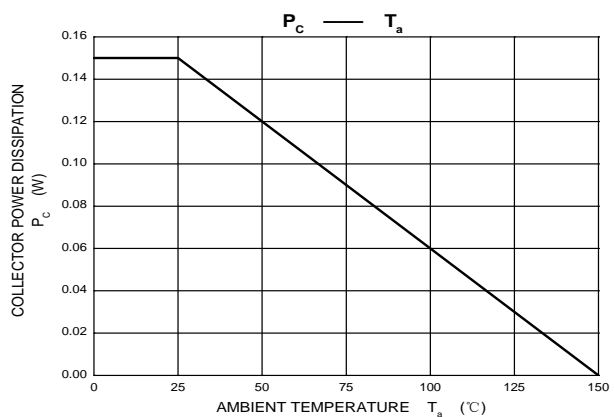
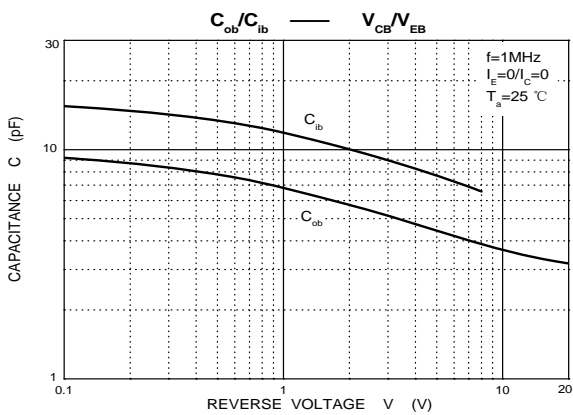
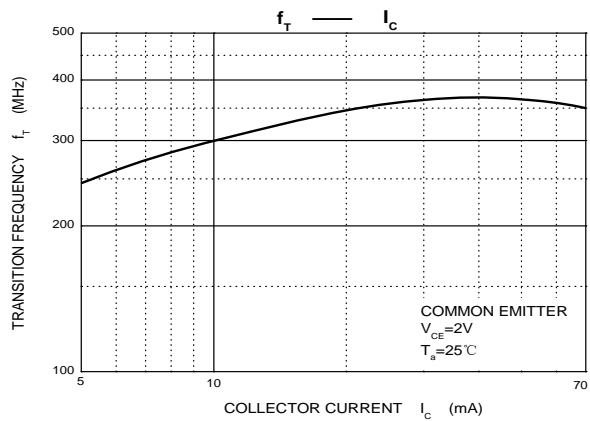
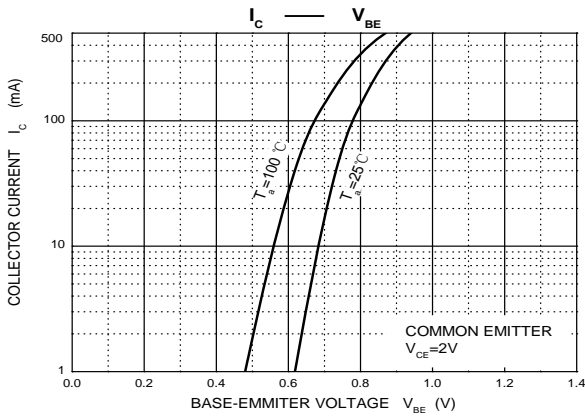
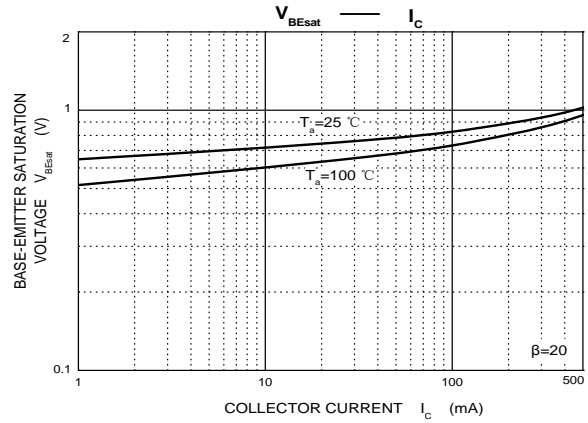
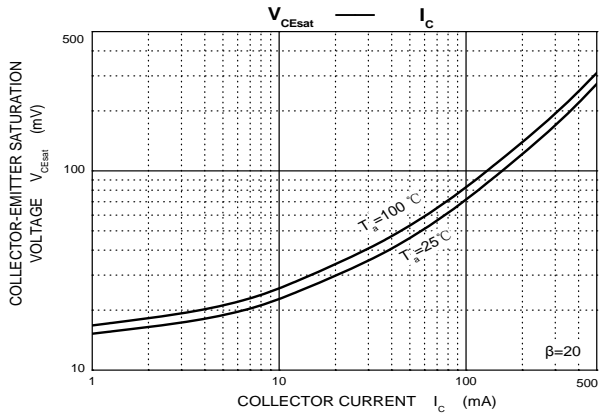
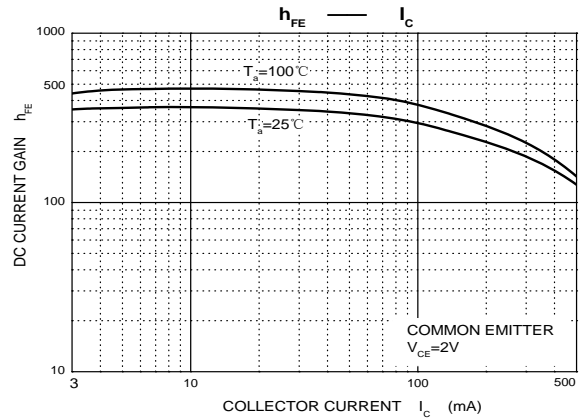
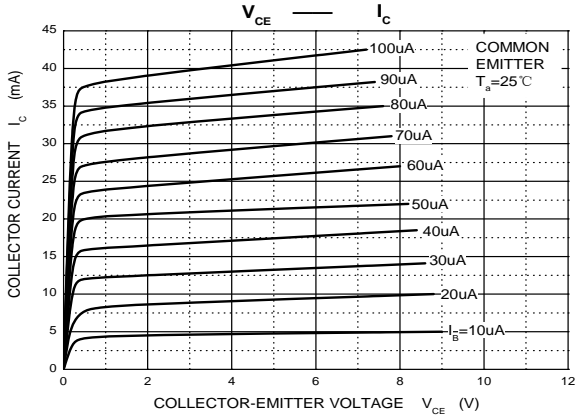
**CHINA BASE**  
INTERNATIONAL

**SOT-363**

**2SC5585DW**

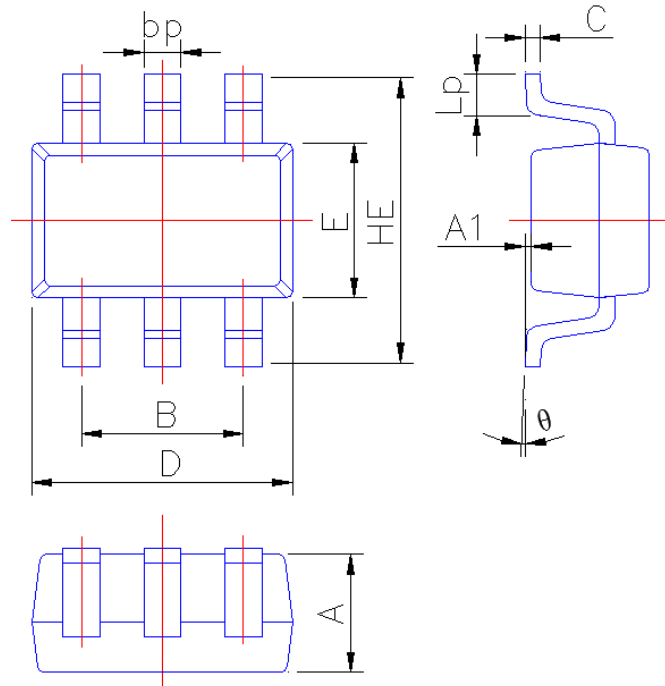


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## SOT-363 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°